UNİSYS

DATE:

April 25, 1994

TO:

J. Denis/311.1

FROM:

K. Sahu/300.1

SUBJECT:

Rediation Report on GOES/SXI Part No. M38510-008-01BCA (LM139)

Control No. 10702

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L. Deemer/300.1

Library/300.1

A. Sharma/311

T. Sinacor!/Aeroflex Laboratories, Inc.

PPM-94-010

A radiation evaluation was performed on LM139 (Quad Voltage Comparator) to determine the total dose tolerance of these parts. A brief aummary of the test results is provided below. For detailed information, refer to Tables 1 through 1V and Figure 1.

The total dose testing was performed using a cobalt-60 gamma ray source. During the radiation testing, four parts were irradiated under bias (see Figure 1 for bias configuration), and one part was used as a control sample. The total dose radiation levels were 10, 20, 30, 50, 75 and 100 krads*. The dose rate was between 0.37 and 1.25 krads/hour, depending on the total dose level (see Table II for radiation schedule). After the 100 krad irradiation, the parts were annealed for 168 hours at 25°C, after which the parts were annealed for 168 hours at 100°C. After each radiation exposure, parts were electrically tested according to the test conditions and the specification limits** listed in Table III.

All parts passed initial electrical measurements. All four irradiated parts passed all electrical measurements up to end including the 75 krad level. At the 100 krad irradiation level, section 3 of all four parts failed to meet the minimum specification level of 50 V/mV for A_OL, with readings ranging from 23.45 to 25.90 V/mV. All irradiated parts passed all other electrical tests at the 100 krad level. After annealing for 168 hours at 25°C, no significant changes were observed in any parameter. After annealing for 168 hours at 100°C, no rebound effects were observed.

Table IV provides the mean and standard deviation values for each parameter after different irradiation exposures and annualing steps. Mean and standard deviation values for all parameters except Icc_5V and Icc_30V are given only for section 3 of the parts since this was the only section in which any failures were observed. Values for other sections are available on request.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

^{*}The term rads, as used in this document, means rads(silicon). All radiation levels cited are cumulative.

**These are manufacturer's non-irradiated data specification limits. No post-irradiation limits were provided by the manufacturer at the time these tests were performed.

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TABLE 1. Part Information

Generic Part Number:

LM139

GDES/SXI

Part Number:

M38510/112-018CA*

GOES/SXI

Control Number:

10702

Charge Number:

C42992

Manufacturer:

PMI

Lot Date Code:

9311

Quantity Tested:

_

Serial Number of

Control Sample:

61

Serial Numbers of

Radiation Samples:

62, 63, 64, 65

Part Function:

Quad Voltage Comparator

Part Technology:

Bipolar

Package Style:

14-pin DIP

Test Equipment:

A540

Test Engineer:

T. Mondy

st No radiation tolerance/hardness was guaranteed by the manufacturer for this part.

TABLE II. Radiation Schedule for LM139

EVENTS	DATE
1) INITIAL ELECTRICAL MEASUREMENTS	03/25/94
2) 10 KRAD [RRAD]ATION (0.50 KRADS/HOUR) POST-10 KRAD ELECTRICAL MEASUREMENT	03/28/94 03/29/94
3) 20 KRAD IRRADIATION (G.50 KRADS/HOUR) POST-20 KRAD ELECTRICAL MEASUREMENT	03/29/94 03/30/94
4) 30 KRAD [RRADIATION (0.50 KRADS/HOUR) POST-30 KRAD ELECTRICAL MEASUREMENT	03/30/94 03/31/94
5) 50 KRAD IRRADIATION (1.00 KRADS/HOUR) POST-50 KRAD ELECTRICAL MEASUREMENT	03/31/94 04/01/94
6) 75 KRAD IRRADIATION (0.37 KRADS/HOUR) POST-75 KRAD ELECTRICAL MEASUREMENT	04/01/94 04/04/94
7) 100 KRAD IRRADIATION (1.25 KRADS/HOUR) POST-100 KRAD ELECTRICAL MEASUREMENT	04/04/94 04/05/94
8) 168-HOUR ANNEALING @25°C POST-168 HOUR ANNEAL ELECTRICAL MEASUREMENTS	04/04/94 04/12/94
9) 168 HOUR ANNEALING @100°C* POST-168 HOUR ANNEAL ELECTRICAL MEASUREMENTS	04/12/94 04/19/94

^{*}High temperature annealing is performed to accelerate long term time dependent effects (TDE), namely, the "rebound" effect, due to the growth of interface states after the radiation exposure. For more information on the need to perform this test, refer to MIL-STO-8830, Method 1019, Para. 3.10.1.

Table III. Electrical Characteristics of LM139

Unless Otherwise Specified: TA =25°C

TEST NAME	SYMBOL	CONDITIONS	LIMITS				
			MUN	MAX			
		SUPPLY CURRENT	<u> </u>	······································			
5V	<u> Iec</u>	+Vcc = 5V, V _{OUT} = 0V	0.000mA	3.000mA			
30V	Icc	+Vcc = 30V, V _{OUT} = 0V	0.000mA	3.000mA			
		INPUT OFFSET TESTS	ĺ				
VOS_5V	v_{IO}	+Vcc = 5V, $VOUT = 1.4V$	-5.00mV	5.00mV			
VOS_30V	VIO	+Vcc = 30V, V _{OUT} = 15V (Note: 1)	-5.00mV	5.00mV			
PSRR	PSRR	$+Vce \approx (5V, 30V), V_{OUT} = 1.4V$	70dB				
P_HB_5V	+I _{IB}	$+Vcc = 5V, V_{OUT} = 1.4V$ (Note: 1)	-100.00nA	-1.000nA			
N_IIB_5V	-IB	$+Vcc = 5V, V_{OUT} = 1.4V$ (Note: 1)	-100.00nA	-1.000nA			
IIOS_5V	I _{IO}	+Vcc = 5V, VOUT = 1.4V (Note: I)	-25.00nA	25.00nA			
P_HB_30V	+JIB	+Vec = 30V, V _{OUT} = 15V (Note: 1)	-100.00nA	-1.000nA			
N_IIB_30V	-I _{IB}	+Vcc = 30V, VOUT = 15V (Note: 1)	-100.00nA	-1.000nA			
HOS_30V	IIO	+Vcc = 30V, VOUT = 15V (Note: 1)	-25.00nA	25.00nA			
AOL		$+Vcc = 5V, V_{OUT} = (11V, 1V)$	50 V/mV				
I_SINK		+Vcc = 5V, VOUT = 1.5V (Note: 2)	6.00mA	<u></u> .			
V_SAT		$+Vcc = 5V, I_{OUT} = 4.0mA \text{ (Note: 2)}$	<u> </u>	400.0mV			
I_LEAK		+Vcc = 30V, V _{OUT} = 30V		0.500цА			

TABLE IV: Summary of Electrical Measurements after
Total Dose Exposures and Annealing for M38510/112-01BCA (LM139) /1

											_										
						Ь—			Tota	l Dose Exposure (ka					ads)	_		Annealing			
		Spec.	•	Initial 10		20		30		50		75		100		168	hrs	168	hrs		
.	(0	Lim.	/3							ļ		i						@25°C		@100°C	
Parameters	<u>-</u>	min	пах	mean		mean	sd	mean	$_{ m sd}$	mean	sd	mean	sd	mean	\mathbf{sd}	mean	sđ	mean	_	mean	
Icc_5V	πA	0_	3.0	0.51		0.50		0.60	. 01	D 60	.01	0,60	.01	0.58	. 01	0 50	. 01	J.58		0.56	
Icc_30V	mA.	D	3.0	0.77	.01	0.75	. 01	0.75	.01	9,75	.01	0.75		0.74	. 01	0 78		0.77		0 71	
VOS_5V	mV	-5.0	5.0	0.17	.08	0.25	.19	0.19	.19	9,19	-20	6, 19		0.22		1.5C		1.04		0.14	
VOS_30V	nV	-5.0	5.0	0.49	. 32	0.26	.11	9.26		0.25		0.25		1.24	.35	3 48	.37	2.91		0.33	-
PSRR	db	70		95.1	3.C	106	9.7	108		1.99	10	17.5		69.4	1.8	83 8		84.1		111	18
P_IIB_5V	n.A	-100	-1.0	•2 9 1	2.3	-33.6	2.3	36.9		-35.6	2.3	-40.0		43.6		69.2		48.4		-42 9	
N_IIB_5V	nA	-105	-1.0	-29.2	2.0	33.4	2.0	95.3		-37,0		- 4C.E		-44.5	1.8	-29.9		. 49			
IIOS_5V	nA	-25	25	0.27		0.35		0.44		0.47		0.57		D. 67		0.74	.72	0.62		-43.3	
P_11B_30V	nA	-100	-1.0	-4.1.4	 -	*35.4		-37.4		39.2		-43.3		-49.3	2.6	-55.9	_	A		0.41	.45
N_IIB_3CV	nA	-100	-1.0	31.6	2.0	-35.5		-37.6		- 39 . 5		-63.5	_	-50.1	1.6	-57.8		-50 4	2.8	-66.4	2.5
I105_30V	nA	-25	25	0.54		0.41	_	0.45		0.54		0.61	.53	0.71	.81	0.85		-57,2		46.6	2.1
AOL	V/mv	50		220		955		296		329		387	59	132		24.6	.96_	0 77		0.6%	.30
I_SINK	mA	5.0		19.3		19 L		i.e.5	_	18.7		18.5		17.8	_			30.8	1.6	618	182
V_SAT	æV		400	222	9.3	222	9.3	727	9.1	223		123	9.2	228		17.0		17.2		17.8	. 54
I_LEAK	ДĄ		0.5	.026		-130	$\overline{}$	e e	_	065		.234		*****	9.1	22,3007,20085		229	8.9	232	9.2
				- Commence				00350 100 100 100 100 100 100 100 100 100 1			.03		. 0.3	052	0	C5 2	0	1.95	.03	.7033	. 03

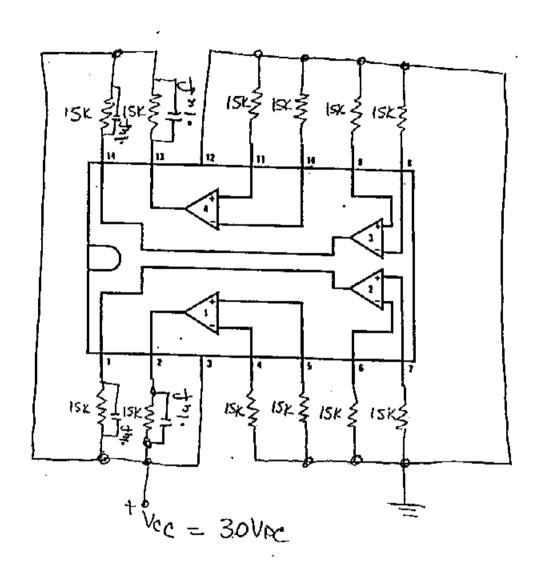
^{1/} The mean and standard deviation values were calculated over the four parts irradiated in this testing. The control sample remained constant throughout the testing and is not included in this table.

Radiation-sensitive parameters were: A_OL.

^{2/} Values for all parameters except Icc_5V and Icc_30V are given only for section 3, which was the only case in which failures occurred. Values for other sections are available on request. Mean and standard deviation values for VOS and IIOS are computed from absolute values.

^{3/} These are manufacturers' non-irradiated data sheet specification limits. No post-irradiation limits were provided by the manufacturer at the time the tests were performed.

Figure 1. Radiation Bias Circuit for LM139



Conditions:

Vcc = 30.0V+0.5VbC R = 15kOhms, 1/2WTa = 25°C